## REMARKS

Claims 1-12 remain present in this application. Claims 1-8 are currently withdrawn from consideration.

Claims 9-12 stand rejected under 35 USC 102(b) as being anticipated by WU et al., U.S. Patent 6,010,934. This rejection is respectfully traversed.

Independent claim 9 recites "a dual polysilicon sidewall spacer gate on the silicon-on-insulator substrate" and "the dual polysilicon sidewall spacer gate separated and symmetric with an insulating layer". The Examiner asserts that WU et al. discloses a dual polysilicon sidewall spacer gate 130 on the silicon-oninsulator substrate (see cols. 3-4, for example). However, the polysilicon spacers 130 taught by WU et al. are not gates of single electron transistors (SETs). The polysilicon spacers 130 taught by WU et al. are used as hard mask to form silicon islands on the substrate (see col. 4, lines 13-18, for example). The hard mask will be removed and is not a functional element of a SET. At most, WU et al. discloses a gate 30 as is shown in FIG. 12. This, however, is not a dual polysilicon sidewall spacer gate. It is therefore respectfully submitted that WU et al. does not teach or suggest the dual polysilicon sidewall spacer gate, because the gate taught by WU et al. is a single gate.

WU et al. also fails to teach or suggest that the insulator is between the dual polysilicon sidewall spacer gate, because a single gate cannot be separated and symmetric with an insulating layer.

In view of the foregoing remarks, it is respectfully submitted that independent claim 9, as well as its dependent claims, are neither taught nor suggested by the prior art utilized by the Examiner. Reconsideration and withdrawal of the 35 USC 102(b) rejection are therefore respectfully requested.

Favorable reconsideration and an early Notice of Allowance are earnestly solicited.

In the event that any outstanding matters remain in this application, the Examiner is invited to contact the undersigned at (703) 205-8000 in the Washington, D.C. area.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fees required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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KM/asc 0941-0783P